

R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	19.7641	N/A	7.1378
RT2	13.1526	N/A	1.4750
RT3	5.1251	N/A	4.9120
RT4	53.4355	N/A	11.4833
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	91.3997 m	N/A	8.0626 m
CT2	36.9001 m	N/A	1.8982 m
CT3	1.9595 m	N/A	426.6082 m
CT4	1.3078	N/A	34.6812 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	6.3880	N/A	2.4901
RF2	25.5351	N/A	11.5612
RF3	12.8664	N/A	9.8891
RF4	46.8675	N/A	1.0868
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	2.0978 m	N/A	1.3718 m
CF2	25.3064 m	N/A	6.2120 m
CF3	257.1027 m	N/A	62.1805 m
CF4	1.2309	N/A	3.1770

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya, IEEE / SEMITHERM 2002

